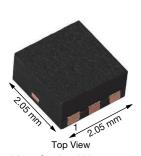


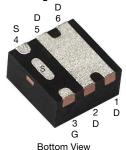
Vishay Siliconix

N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^a	Q _g (TYP.)						
150	0.177 at V _{GS} = 10 V	7.7							
	0.185 at V _{GS} = 7.5 V	7.6	4.3 nC						
	0.250 at V _{GS} = 6 V	4							

PowerPAK® SC-70-6L Single





Marking Code: AV **Ordering Information:**

SiA446DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- ThunderFET® technology optimizes balance of R_{DS(on)}, Q_g, Q_{sw} and Q_{oss}
- 100 % Rq and UIS tested
- · Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

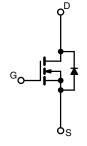




HALOGEN FREE

APPLICATIONS

- DC/DC converters / boost converters
- Synchronous rectification
- · Power management
- LED backlighting



N-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	150	V	
Gate-Source Voltage		V _{GS}	± 20	V	
	T _C = 25 °C		7.7		
Continuous Dunis Comment (T. 150 °C)	T _C = 70 °C		6.2		
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	3.3 ^{b, c}		
	T _A = 70 °C		2.6 b, c		
Pulsed Drain Current (t = 100 μs)		I _{DM}	10	A	
Cantinua de Carres Dunia Dia da Comuna	T _C = 25 °C	,	12		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.9 b, c		
Single Pulse Avalanche Current	. 0.111	I _{AS}	7		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	2.5	mJ	
	T _C = 25 °C		19		
Marian and Danier Distriction	T _C = 70 °C		12	14/	
Maximum Power Dissipation	T _A = 25 °C	P _D	3.5 b, c	W	
	T _A = 70 °C		2.2 b, c		
Operating Junction and Storage Temperature R	Range	T _J , T _{stg}	-55 to 150	00	
Soldering Recommendations (Peak Temperatur	·e) ^{d, e}		260	°C	

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
		R _{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	C/VV				

Notes

- a. Based on $T_C = 25$ °C.
- b. Surface mounted on 1" x 1" FR4 board.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

 Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.

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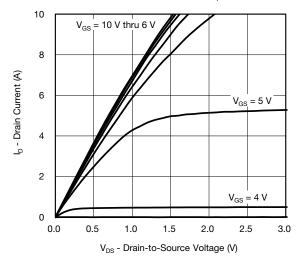
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					l	<u> </u>
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	150	-	_	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	•	-	73	-	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \mu A$	_	-6	-	mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5	-	3.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	_	-	± 100	nA
Ğ		V _{DS} = 150 V, V _{GS} = 0 V	-	-	1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V, T _J = 55 °C	-	-	10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10	-	-	Α
	(*)	V _{GS} = 10 V, I _D = 3 A	-	0.145	0.177	
Drain-Source On-State Resistance a	R _{DS(on)}	V _{GS} = 7.5 V, I _D = 2 A	-	0.151	0.185	Ω
	`	$V_{GS} = 6 \text{ V}, I_{D} = 1 \text{ A}$	-	0.165	0.250	
Forward Transconductance a	9 _{fs}	V _{DS} = 10 V, I _D = 3 A	-	6	-	S
Dynamic ^b			·		L	
Input Capacitance	C _{iss}		-	230	-	
Output Capacitance	C _{oss}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	47	-	pF
Reverse Transfer Capacitance	C _{rss}		-	8	-	
·		V _{DS} = 75 V, V _{GS} = 10 V, I _D = 3.5 A	-	5.3	8	
Total Gate Charge	Qg		-	4.3	6.5	1
Gate-Source Charge	Q _{as}	$V_{DS} = 75 \text{ V}, V_{GS} = 7.5 \text{ V}, I_D = 3.5 \text{ A}$	-	1.2	-	nC
Gate-Drain Charge	Q _{qd}		-	1.8		
Output Charge	Q _{oss}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$	-	8.5		
Gate Resistance	R_g	f = 1 MHz	0.5	2.3	4.6	Ω
Turn-On Delay Time	t _{d(on)}		-	5	10	
Rise Time	t _r	$V_{DD} = 75 \text{ V}, R_L = 29 \Omega,$	-	13	25	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 2.6 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	10	20	
Fall Time	t _f		-	10	20	
Turn-On Delay Time	t _{d(on)}		-	10	20	ns
Rise Time	t _r	$V_{DD} = 75 \text{ V}, R_L = 29 \Omega,$	-	40	80	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 2.6 \text{ A}, V_{GEN} = 6 \text{ V}, R_g = 1 \Omega$	-	5	10	
Fall Time	-4(011)					
Drain-Source Body Diode Characteristic	:s				l	1
Continuous Source-Drain Diode Current	Is	T _C = 25 °C	-	-	12	А
Pulse Diode Forward Current (t = 100 μs)	I _{SM}	-	-	-	10	
Body Diode Voltage	V _{SD}	I _S = 3.5 A	-	0.9	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	-	-	51	100	ns
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = 3.5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s},$	_	100	200	nC
Reverse Recovery Fall Time	ta	$T_{J} = 25 ^{\circ}\text{C}$		43	-	
Reverse Recovery Rise Time	t _b		_	8	-	ns

Notes

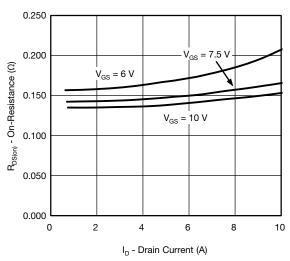
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

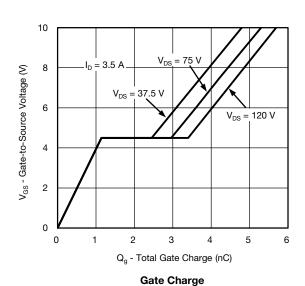


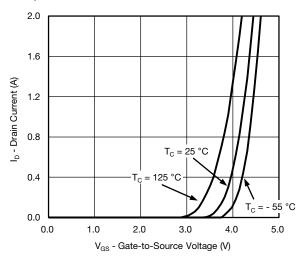


Output Characteristics

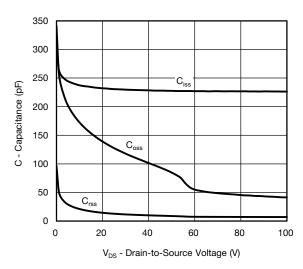


On-Resistance vs. Drain Current and Gate Voltage

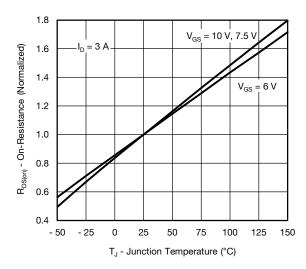




Transfer Characteristics

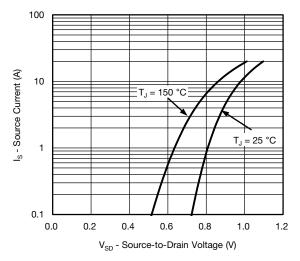


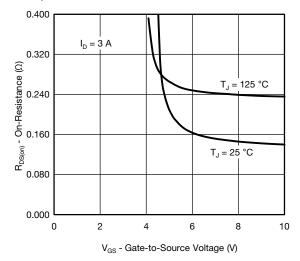
Capacitance



On-Resistance vs. Junction Temperature

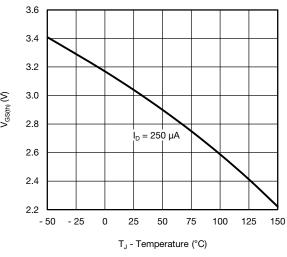


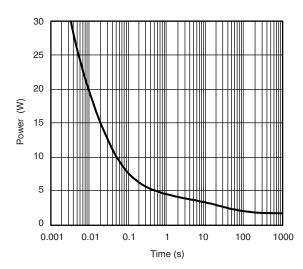




Source-Drain Diode Forward Voltage

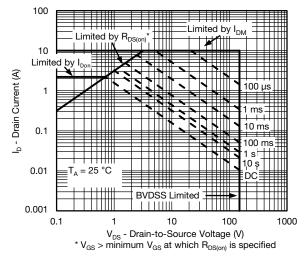
On-Resistance vs. Gate-to-Source Voltage





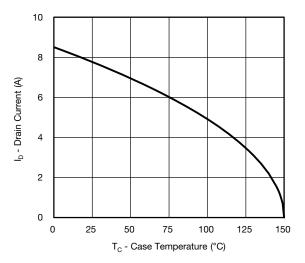
Threshold Voltage

Single Pulse Power, Junction-to-Ambient

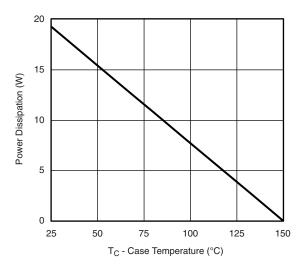


Safe Operating Area, Junction-to-Ambient





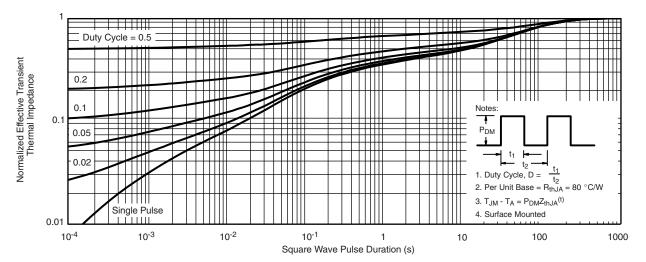
Current Derating*



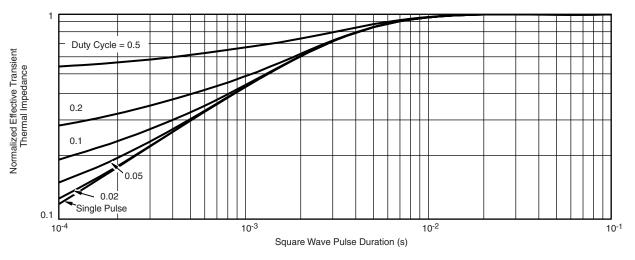
Power, Junction-to-Case

^{*} The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

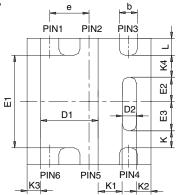
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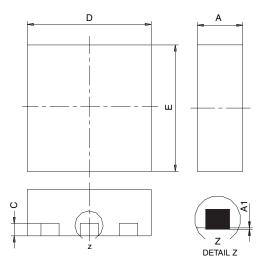
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

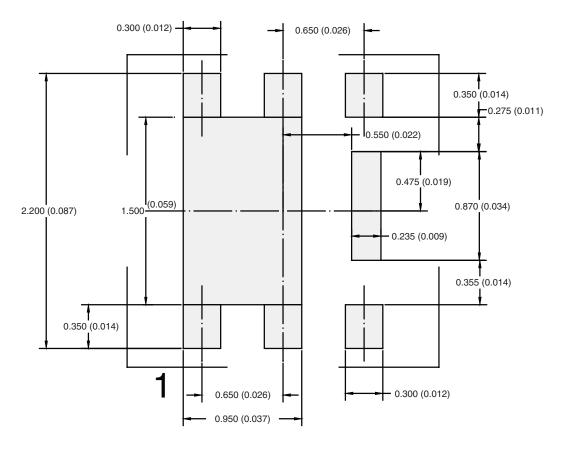
	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP	1		0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP	1	0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP 0.009 TYP			0.252 TYP 0.010 TYP				1			
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
FCN: C-07431 – Bey C. 06-Aug-07												

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



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Revision: 02-Oct-12 Document Number: 91000

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